BTA16, BTB16 and T16 Series

Table 3:	Absolute	Maximum	Ratings
----------	----------	---------	---------

Symbol	Parame	Parameter					
I _{T(RMS)}	RMS on-state current (full sine wave)	$\begin{array}{ c c c } D^2 PAK / & & T_c = 100^{\circ}C \\ TO-220AB & & \end{array}$		16	А		
	wave)	TO-220AB Ins.	$T_c = 15^{\circ}C$				
I _{TSM}	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	160	А		
ISM	current (full cycle, T_j initial = 25°C)	F = 60 Hz	t = 16.7 ms	168	~		
l²t	I ² t Value for fusing	t _p = 10 ms	144	A²s			
dl/dt	Critical rate of rise of on-state current I_G = 2 x I_{GT} , $t_r \leq$ 100 ns	F = 120 Hz	T _j = 125°C	50	A/µs		
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage	t _p = 10 ms	$T_j = 25^{\circ}C$	V _{DSM} /V _{RSM} + 100	V		
I _{GM}	Peak gate current $t_p = 20 \ \mu s$ $T_j = 125^{\circ}C$			4	А		
P _{G(AV)}	Average gate power dissipation	1	W				
T _{stg} T _j	Storage junction temperature range Operating junction temperature range	- 40 to + 150 - 40 to + 125	°C				

Tables 4: Electrical Characteristics ($T_j = 25^{\circ}C$, unless otherwise specified)

■ SNUBBERLESS and Logic Level (3 quadrants)

Symbol	Test Conditions	est Conditions Quadrant		T16	BTA16 / BTB16			Unit
Symbol	Test conditions	Quadram		T1635	SW	CW	BW	Onit
I _{GT} (1)	$V_{\rm D} = 12 \text{V} \text{R}_{\rm I} = 33 \Omega$	- -	MAX.	35	10	35	50	mA
V _{GT}		- -	MAX.		1	.3		V
V _{GD}			MIN.		0	.2		V
I _H (2)	I _T = 500 mA		MAX.	35	15	35	50	mA
I,	I _G = 1.2 I _{GT}	- 1 2 I	MAX.	50	25	50	70	mA
·L		II	101/1/1	60	30	60	80	
dV/dt (2)	$V_D = 67 \% V_{DRM}$ gate open	T _j = 125°C	MIN.	500	40	500	1000	V/µs
	(dV/dt)c = 0.1 V/µs	T _j = 125°C		-	8.5	-	-	
(dl/dt)c (2)	(dV/dt)c = 10 V/µs	T _j = 125°C	MIN.	-	3.0	-	-	A/ms
	Without snubber	$T_j = 125^{\circ}C$		8.5	-	8.5	14	

57

Symbol	Symbol Test Conditions			BTA16 / BTB16		Unit	
Symbol	Test conditions	Quadrant		С	В		
I _{GT} (1)	$V_{\rm D} = 12 V R_{\rm L} = 33 \Omega$	- - V	MAX.	25 50	50 100	mA	
V _{GT}		ALL	MAX.	1.3		V	
V _{GD}	$V_D = V_{DRM} R_L = 3.3 \text{ k}\Omega T_j = 125^\circ C$	ALL	MIN.	0.2		V	
I _H (2)	I _T = 500 mA		MAX.	25	50	mA	
ΙL	I _G = 1.2 I _{GT}	I - III - IV	MAX.	40	60	mA	
·L		II	MIAX.	80	120		
dV/dt (2)	$V_{D} = 67 \% V_{DRM}$ gate open	T _j = 125°C	MIN.	200	400	V/µs	
(dV/dt)c (2)	(dl/dt)c = 7 A/ms	$T_j = 125^{\circ}C$	MIN.	5	10	V/µs	

Standard (4 quadrants)

Table 5: Static Characteristics

Symbol	Test Co		Value	Unit	
V _T (2)	$I_{TM} = 22.5 \text{ A}$ $t_p = 380 \ \mu \text{s}$	$T_j = 25^{\circ}C$	MAX.	1.55	V
V _{to} (2)	Threshold voltage	T _j = 125°C	MAX.	0.85	V
R _d (2)	Dynamic resistance	T _j = 125°C	MAX.	25	mΩ
I _{DRM}	V _{DBM} = V _{BBM}	$T_j = 25^{\circ}C$	MAX.	5	μA
I _{RRM}		T _j = 125°C		2	mA

Note 1: minimum I_{GT} is guaranted at 5% of I_{GT} max.

Note 2: for both polarities of A2 referenced to A1.

Table 6: Thermal resistance

Symbol		Parameter			Unit		
B (1.)	-c) Junction to case (AC)		D ² PAK / TO-220AB		D ² PAK / TO-220AB	1.2	°C/W
R _{th(j-c)}			TO-220AB Insulated	2.1	0/00		
Burr	Junction to ambient		D ² PAK	45	°C/W		
R _{th(j-a)}		<u></u>	TO-220AB / TO-220AB Insulated	60	0/00		

S = Copper surface under tab.



Figure 1: Maximum power dissipation versus RMS on-state current (full cycle)

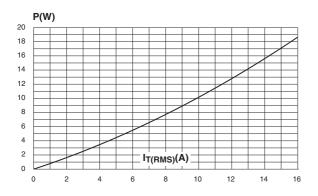


Figure 3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm) (full cycle)

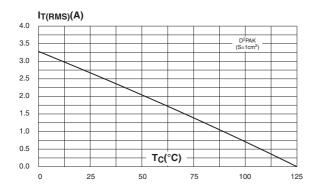


Figure 5: On-state characteristics (maximum values)

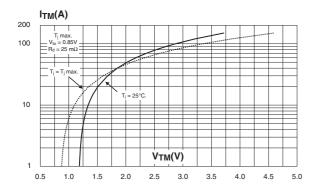


Figure 2: RMS on-state current versus case temperature (full cycle)

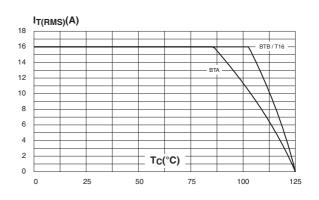


Figure 4: Relative variation of thermal impedance versus pulse duration

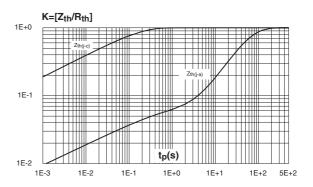
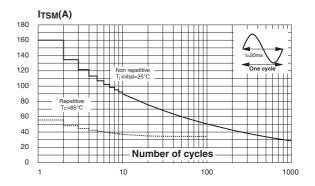


Figure 6: Surge peak on-state current versus number of cycles



/

Figure 7: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10$ ms and corresponding value of l^2t

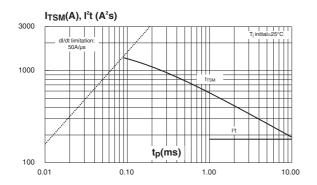


Figure 9: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values) (Snubberless & Logic level types)

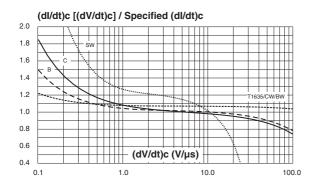


Figure 11: D²PAK Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: 35 µm)

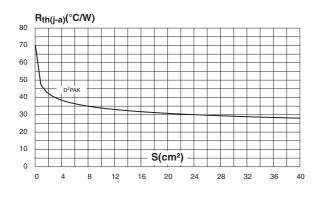




Figure 8: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

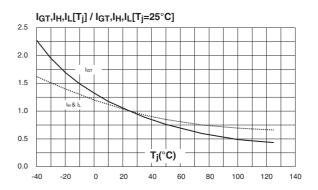
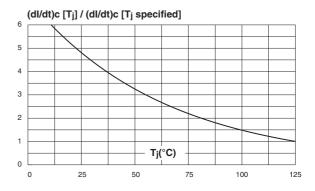


Figure 10: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values) (Standard types)



BTA16, BTB16 and T16 Series

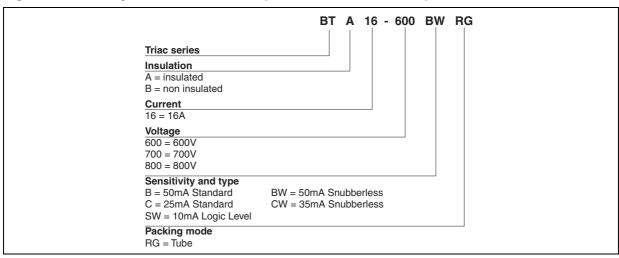




Figure 13: Ordering Information Scheme (T16 series)

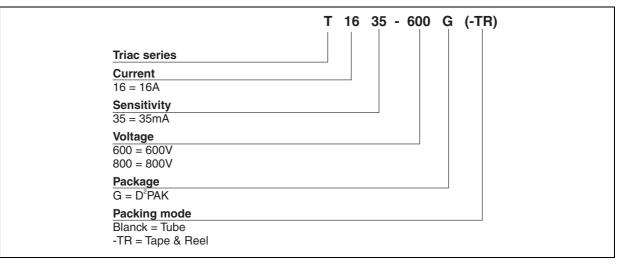
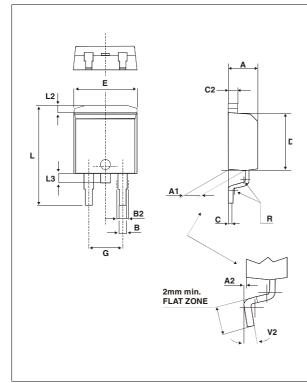


Table 7: Product Selector

Part Numbers		Voltage (xxx	x)	Sensitivity	Туре	Package
Fait Nullibers	600 V	700 V	800 V	Sensitivity	туре	Fackage
BTA/BTB16-xxxB	Х	Х	Х	50 mA	Standard	TO-220AB
BTA/BTB16-xxxBW	Х	Х	Х	50 mA	Snubberless	TO-220AB
BTA/BTB16-xxxC	Х	Х	Х	25 mA	Standard	TO-220AB
BTA/BTB16-xxxCW	Х	Х	Х	35 mA	Snubberless	TO-220AB
BTA/BTB16-xxxSW	Х	Х	Х	10 mA	Logic level	TO-220AB
T1635-xxxG	Х		Х	35 mA	Snubberless	D ² PAK

/

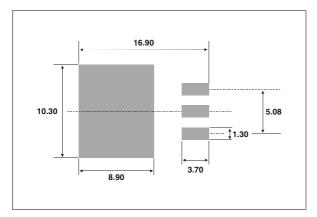
BTB: non insulated TO-220AB package



			DIMEN	SIONS	1	
REF.	Mi	llimete	ers		Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.048	0.055	
С	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
Е	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R		0.40			0.016	
V2	0°		8°	0°		8°

Figure 14: D²PAK Package Mechanical Data

Figure 15: D²PAK Foot Print Dimensions (in millimeters)





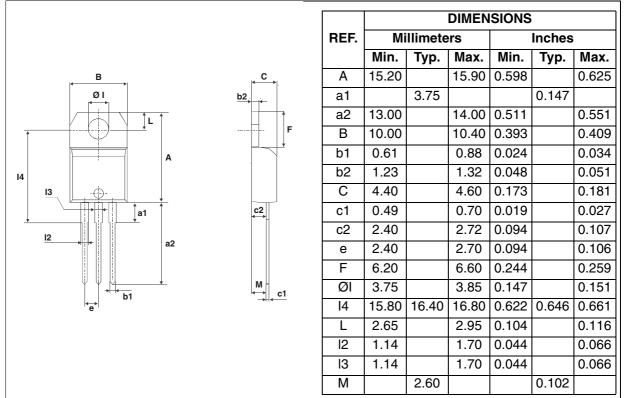


Figure 16: TO-220AB Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 8: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BTA/BTB16-xxxyzRG	BTA/BTB16xxxyz	TO-220AB	2.3 g	50	Tube
T1635-xxxG	T1635xxxG	D ² PAK	1.5 g	50	Tube
T1635-xxxG-TR	T1635xxxG	DTAK	1.5 g	1000	Tape & reel

Note: xxx = voltage, yy = sensitivity, z = type

Table 9: Revision History

Date	Revision	Description of Changes
Oct-2002	6A	Last update.
13-Feb-2006	7	TO-220AB delivery mode changed from bulk to tube. ECOPACK statement added.

47/

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America www.st.com

